

## ABSTRACT OF THE DISCLOSURE

Disclosed is a pattern forming method, in which a mask blank for preparation of a photomask is exposed in a desired pattern to form a mask pattern on the mask blank. Position measuring marks are formed on the diagonally facing corners of a main surface of the mask blank to detect a defect on the main surface of the mask blank. The relative positions of the detected defect and the mask pattern that is to be formed on the mask blank are compared, and the pattern position is selected such that the defect overlaps with the pattern. Then, the position measuring marks are measured to calculate the exposure position, and exposure treatment is applied to the selected position.

5

10

15

20

25

30

35

40

45

50

55

60

65

70

75

80

85

90

95